

S.No. of Question Paper : 7974

Unique Paper Code : 2513010021

Name of the Course : B.Sc.(H) Electronics (GE)

Name of the Paper : CMOS Digital VLSI Design

Semester : VII

Duration : 3 hours

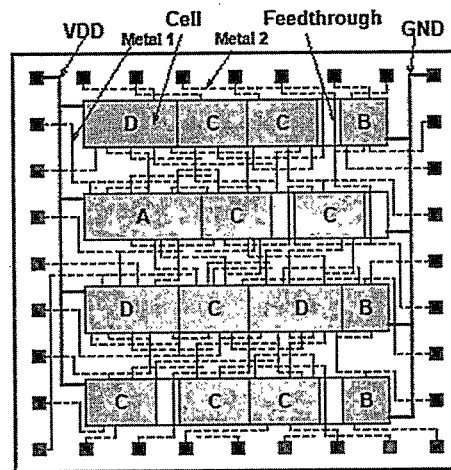
Maximum Marks : 90

Instruction for Candidates

1. There are seven questions in all, out of which attempt any five questions.
2. All questions carry equal marks.
3. First Question is Compulsory.

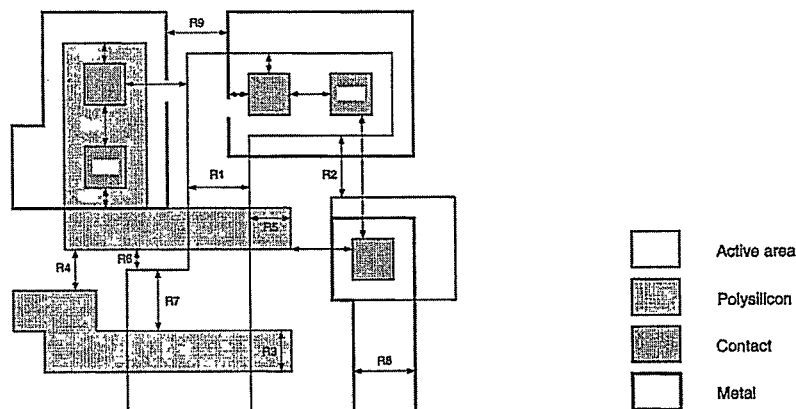
- Q1 a) What are the key differences in VHDL and Verilog?
b) What are the main parts of a VHDL code.
c) Write a short code for a two input AND gate with delay of 5 units in Verilog.
d) What are four basic values of Verilog value set?
e) Why is refresh circuitry needed in a DRAM cell?
f) What is LVS and parameter extraction in VLSI? 3x6
- Q2 a) Compare the three types of modelling in VHDL. Discuss briefly with examples. 6
b) Write a code in VHDL to implement Full Adder. 7
c) Describe the various data objects in VHDL. 5
- Q3 a) Compare the statements 'WHEN ELSE' and 'WITH WHEN SELECT' with the help of an example. 6
b) Discuss with the help of an example, the role of components and port mapping in Structural Modelling in VHDL. 7
c) Briefly explain the various relational and logical operators in VHDL. 5
- Q4 a) What will be the execution sequence and output of statements in the code of a stimulus block given below:
- ```
module stimulus;
 reg x,y,a,b,m;
 initial
 m=1'b0;
 initial
 begin
 #5 a=1'b1;
 #25 b=1'b0;
 end
 initial
 begin
 #10 x=1'b0;
 #25 y=1'b1;
 end
 initial
 #50 $finish;
endmodule
```
- b) Write a Verilog code for 4X1 MUX using gate level modelling. 7  
c) Describe Port connection rules in Verilog. 5

- Q5 a) How conditional operators can be used in Verilog for behavioural modelling. Explain with example. 7
- b) Briefly describe hierarchy and the four levels of abstraction in Verilog. 6
- c) When we have many alternatives to choose which one is better using nested if-else-if or case statement in Verilog? Explain with examples. 5
- Q6 a) What are the advantages and disadvantages of a 6T full CMOS SRAM? 6
- b) What is access time penalty in 6T Full CMOS SRAM cell and how is it reduced? 5
- c) Draw and explain the typical voltage waveforms associated with 3-T DRAM cell during four consecutive operations: write "1," read "1," write "0," and read "0." 7
- Q7 a)



Based on the given layout diagram, What is the CMOS VLSI design methodology used? What does A,B,C and D signify? Explain the function of each labelled component. 6

- b) What are the various steps involved in the ASIC Design Flow? Elaborate on Front-end and Back-end design. 6
- c)



Identify the regions from R1 to R9 and provide their typical value based on the  $\lambda$  based scaling design rules 6